



DMP2100U

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	Package	I _D T _A = +25°C
	38mΩ @ V _{GS} = -10V		-4.3A
-20V	43mΩ @ V _{GS} = -4.5V	SOT23	-4.0A
	75mΩ @ V_{GS} = -2.5V		-2.8A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

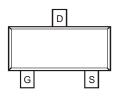
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

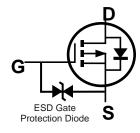




SOT23

Top View





Top View Internal Schematic

Equivalent Circuit (Note 5)

Ordering Information (Notes 5 & 6)

Part Number	Compliance	Case	Packaging
DMP2100U-7	Standard	SOT23	3,000/Tape & Reel
DMP2100UQ-7	Automotive	SOT23	3,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

A duction tive products are AEC-Q101 qualified and are PPAP capable. Please refer to http://www.diodes.com/product_compliance_definitions.html.

5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating

(given on page 2) can be applied.

6. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

35P	ΥM

35P = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Year	2008	~	2017	2018	3 201	9 20)20	2021	202	22	2023	2024	2025
Code	V	~	E	F	G		H		J		K	L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Ju	l Au	g	Sep	Oct	Nov	Dec
Code		0	0		-	6	7	0		~	0	NI	

DMP2100U Document number: DS35718 Rev. 7 - 2 Downloaded from Arrow.com.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage (Note 7)	V _{GSS}	±10	V		
	Steady State	T _A = +25°C T _A = +70°C	Ι _D	-4.3 -3.4	A
Continuous Drain Current (Note 9) $V_{GS} = -10V$	t<5s	T _A = +25°C T _A = +70°C	I _D	-5.5 -4.3	A
Maximum Continuous Body Diodes Forward Curr	ent (Note 9)	ls	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = '	1%)		I _{DM}	-30	А
Pulsed Body Diodes Forward Current (10µs Pulse	e, Duty Cyc	le = 1%)	I _{SM}	-30	А

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Dower Dissinction (Note 9)	T _A = +25°C	Р	0.8	W	
Total Power Dissipation (Note 8)	$T_A = +70^{\circ}C$	PD	0.5		
Thermal Desistance, Junction to Ambient (Note 8)	Steady State	D	161	°C/W	
hermal Resistance, Junction to Ambient (Note 8)	t<5s	R _{0JA}	96		
Total Power Dissipation (Note 9)	T _A = +25°C	P	1.3	W	
Total Power Dissipation (Note 9)	T _A = +70°C	PD	0.8		
Thermal Resistance, Junction to Ambient (Note 9)	Steady State	D	99	°C/W	
Thermal Resistance, Junction to Ambient (Note 9)	t<5s	$R_{\theta JA}$	60		
Thermal Resistance, Junction to Case (Note 9)		R _{θJC}	15		
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +150	°C	

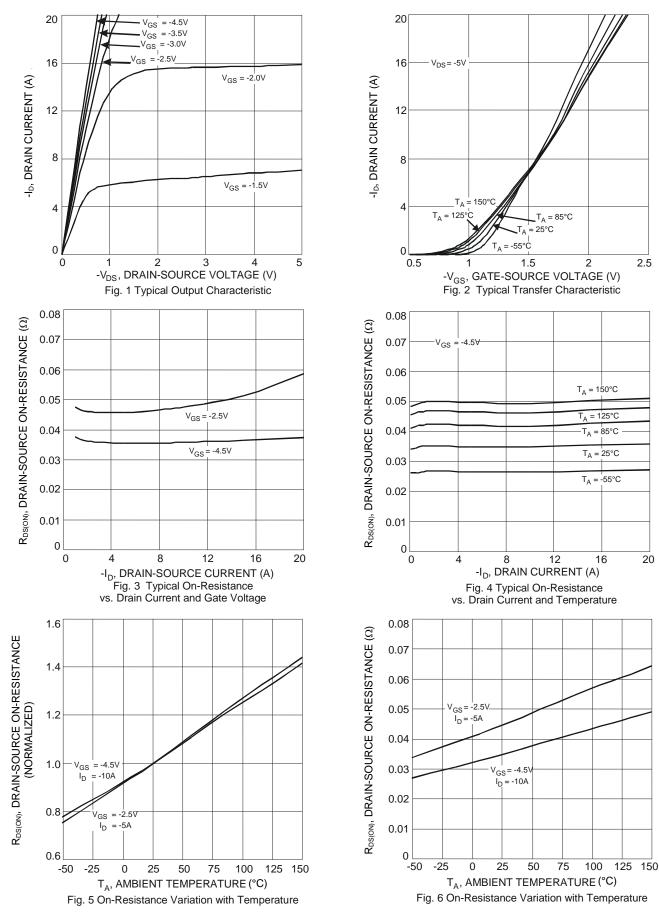
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)	Cymbol		1.76	max	Onic	Test condition
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	IGSS		—	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 10)						÷
Gate Threshold Voltage	V _{GS(TH)}	-0.3	_	-1.4	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			25	38		$V_{GS} = -10V, I_D = -3.5A$
Static Drain-Source On-Resistance	D		29	43	mΩ	$V_{GS} = -4.5V, I_D = -3A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	37	75	11122	V _{GS} = -2.5V, I _D = -1A
		_	47	—		V _{GS} = -1.8V, I _D = -0.5A
Forward Transfer Admittance	Y _{fs}	—	3	—	S	$V_{DS} = -5V, I_D = -4A$
DYNAMIC CHARACTERISTICS (Note 11)						·
Input Capacitance	Ciss		216	—	pF	\/ 45\/ \/ Q\/
Output Capacitance	Coss		90	-	pF	−V _{DS} = -15V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		24	—	pF	
Gate Resistnace	Rg	_	250	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 11)						·
Total Gate Charge	Qg		9.1	-	nC	
Gate-Source Charge	Q _{gs}	_	1.6	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V$
Gate-Drain Charge	Q _{qd}	_	2.0	—	nC	$-I_D = -4A$
Turn-On Delay Time	t _{D(ON)}	—	80	—	ns	
Turn-On Rise Time	t _R	-	155	—	ns	V _{DS} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(OFF)}		688	—	ns	$R_D = 2.5\Omega, R_G = 3.0\Omega$
Turn-Off Fall Time	t _F		423	—	ns	7

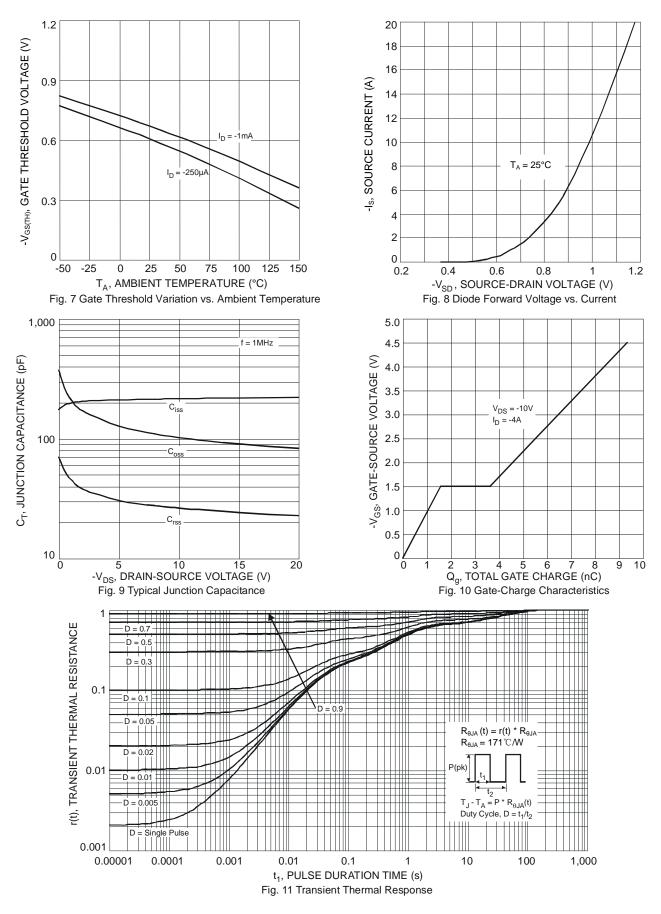
7. AEC-Q101 V_{GS} maximum is $\pm 9.6V.$ Notes:

AEC-Q101 V_{GS} maximum is ±9.6V.
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.







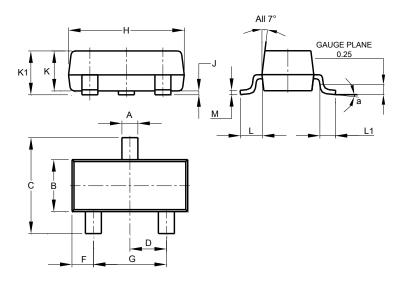




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

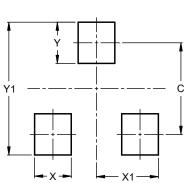
SOT23



	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
К	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
М	0.085	0.150	0.110						
а	0°	8°							
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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